

TSM3457 30V P-Channel MOSFET



SOT-26

654

Pin Definition:

- 1. Drain 6. Drain 2. Drain 5, Drain
- 3. Gate 4. Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
-30	60 @ V _{GS} = 10V	-5
	100 @ V _{GS} = 4.5V	-3.7

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

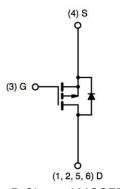
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing	
TSM3457CX6 RF	SOT-26	3Kpcs / 7" Reel	

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	-5	Α	
Pulsed Drain Current		I _{DM}	-20	Α	
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	-1.7	Α	
Maximum Power Dissipation	Ta = 25°C	В	2.0	W	
	Ta = 70°C	P _D	1.3	v v	
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit	
Junction to Case Thermal Resistance	$R\Theta_{JC}$	30	°C/W	
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	80	°C/W	

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.

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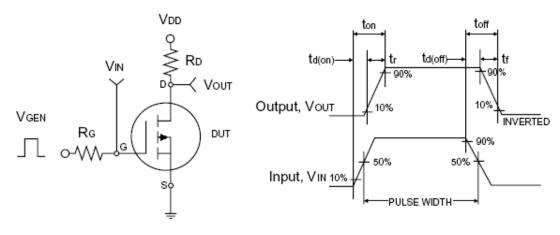


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV _{DSS}	-30		I	V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.0	-1.5	-3.0	V	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}	I		±100	nA	
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I _{DSS}	I		-1.0	μA	
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -10V$	I _{D(ON)}	-20		I	Α	
Drain-Source On-State Resistance ^a	$V_{GS} = -4.5V, I_{D} = -3.7A$		I	82	100	mΩ	
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -5A$	R _{DS(ON)}	I	50	60		
Forward Transconductance ^a	$V_{DS} = -15V, I_{D} = -5A$	g _{fs}	I	10	I	S	
Diode Forward Voltage	$I_S = -1.7A$, $V_{GS} = 0V$	V_{SD}	I	-0.8	-1.2	V	
Dynamic ^b							
Total Gate Charge	$V_{DS} = -15V, I_D = -3.7A,$	Q_g		9.52			
Gate-Source Charge	$V_{DS} = -15V, I_D = -3.7A,$ $V_{GS} = -10V$	Q_gs		3.43		nC	
Gate-Drain Charge	V _{GS} = -10V	Q_{gd}		1.71			
Input Capacitance	\/ - 45\/ \/ - 0\/	C _{iss}	-	551.57	-		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}	I	90.96	I	pF	
Reverse Transfer Capacitance	1 - 1.0IVIM2	C _{rss}	I	60.79	I		
Switching ^c							
Turn-On Delay Time	V - 45V D - 450	t _{d(on)}	I	10.8	I		
Turn-On Rise Time	$V_{DD} = -15V, R_L = 15\Omega,$	t _r		2.33	-	nS	
Turn-Off Delay Time	$I_D = -1A, V_{GEN} = -10V,$ $R_G = 6\Omega$	t _{d(off)}		22.53	-	110	
Turn-Off Fall Time	1XG = 022	t _f		3.87			

Notes:

- a. pulse test: PW \leq 300µS, duty cycle \leq 2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

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20

12

0

2

lo - Drain Current (A)

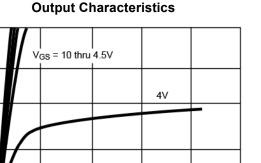
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

3V

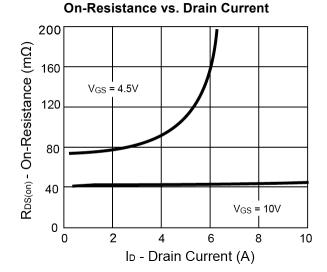
6

8

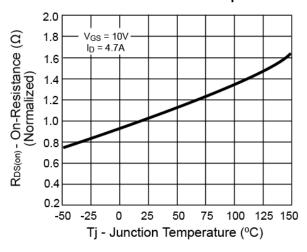
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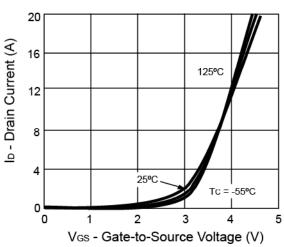
V_{DS} - Drain-to-Source Voltage (V)



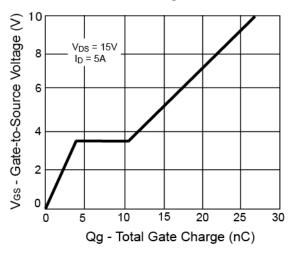
On-Resistance vs. Junction Temperature



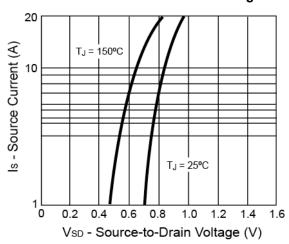




Gate Charge



Source-Drain Diode Forward Voltage



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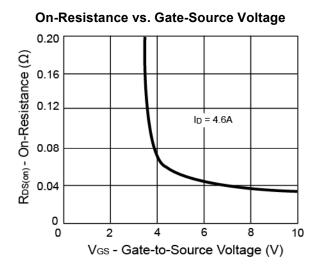


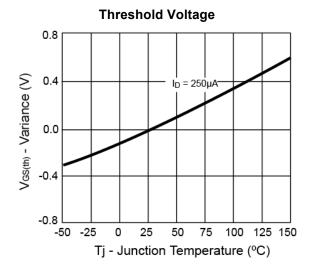






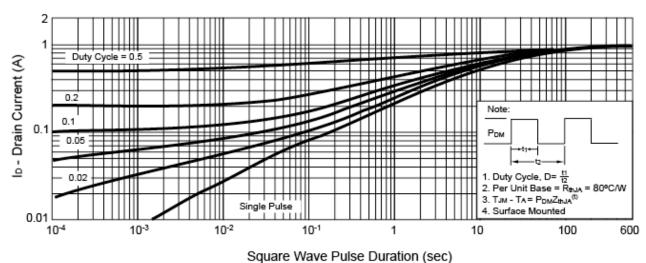
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)





Single Pulse Power 70 60 50 40 20 10 0 10-2 10-1 0 1 10 30 Tiime (sec)

Normalized Thermal Transient Impedance, Junction-to-Ambient



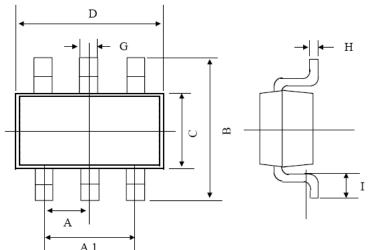
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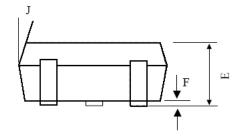




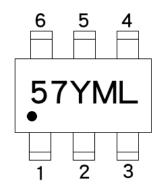
SOT-26 Mechanical Drawing



_							
	SOT-26 DIMENSION						
DIM	MILLIMETERS		INCHES				
DIM	MIN	TYP	MAX	MIN	TYP	MAX	
Α	0.95 BSC			0	.0374 BS	С	
A1	1.9 BSC			0	.0748 BS	С	
В	2.60	2.80	3.00	0.1024	0.1102	0.1181	
С	1.40	1.50	1.70	0.0551	0.0591	0.0669	
D	2.80	2.90	3.10	0.1101	0.1142	0.1220	
Е	1.00	1.10	1.20	0.0394	0.0433	0.0472	
F	0.00		0.10	0.00		0.0039	
G	0.35	0.40	0.50	0.0138	0.0157	0.0197	
Н	0.10	0.15	0.20	0.0039	0.0059	0.0079	
I	0.30		0.60	0.0118		0.0236	
J	5°		10°	5°		10°	



Marking Diagram



57 = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

5/6

L = Lot Code

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